

# Dielectric Metasurface Concentrators

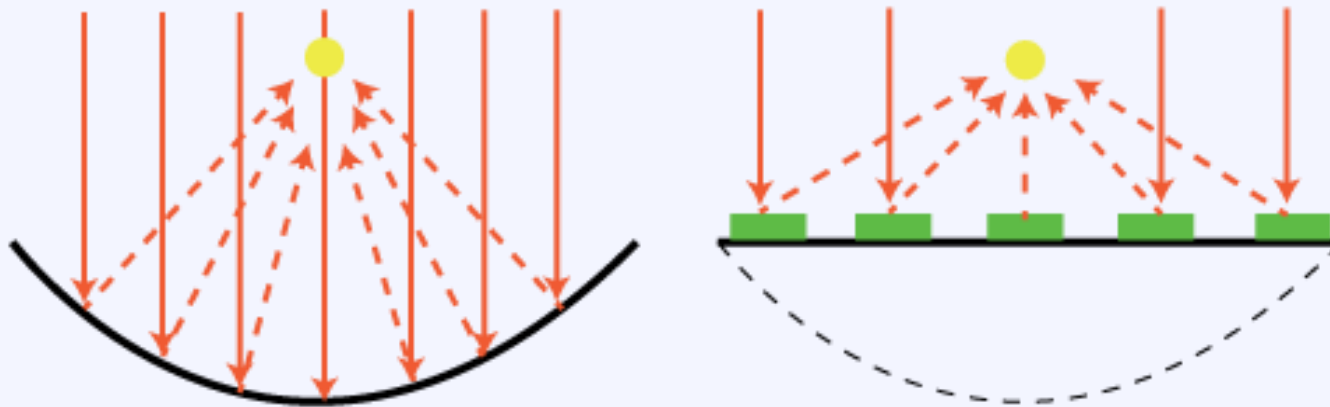
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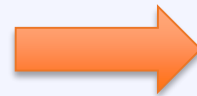
JULIUS YELLOWHAIR

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# Planar structured interface collector



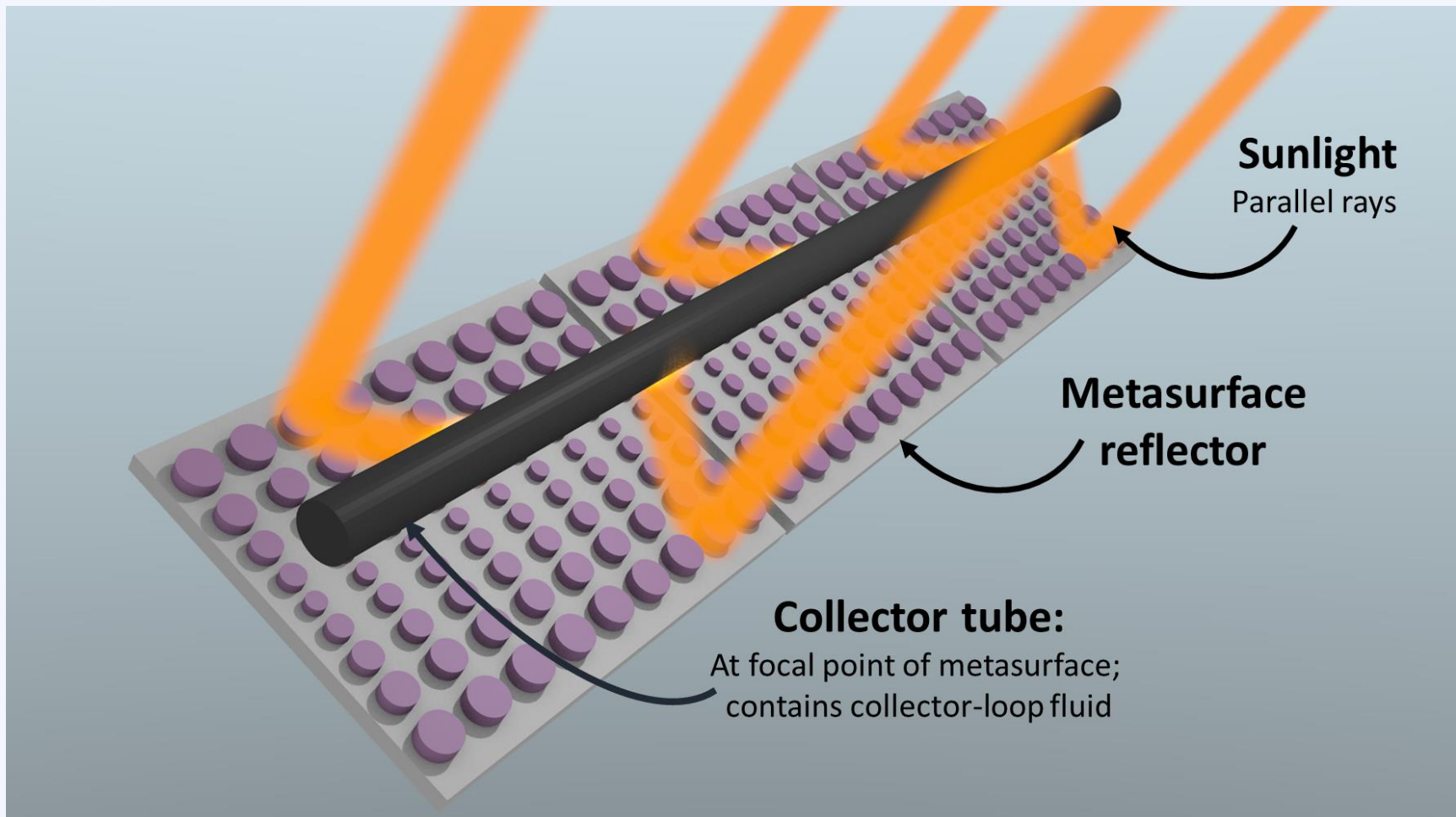
Parabolic in space



Parabolic in phase

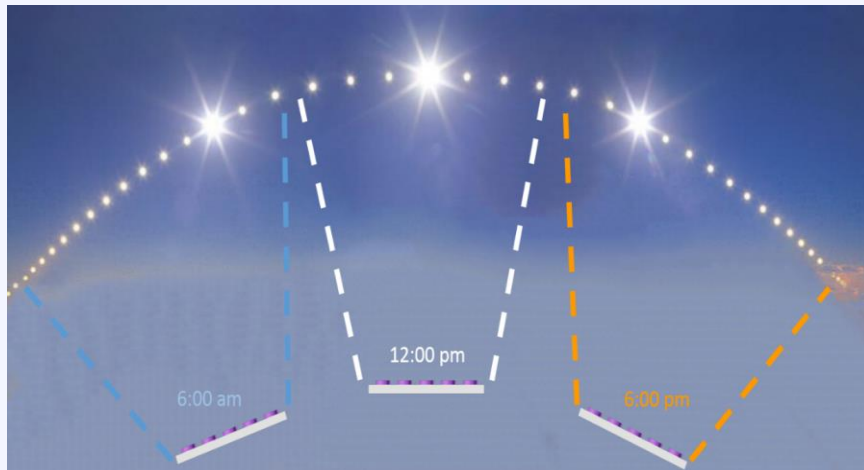
$$\Phi(x) = k_0 \left( \sqrt{x^2 + f^2} - f \right)$$

# Dielectric Metasurface Trough Collector



Reduce needed area, Wider acceptance angle, Reduced tracking.

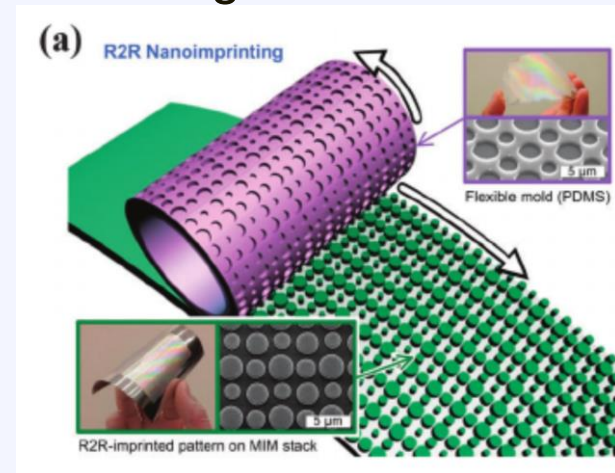
# Motivation



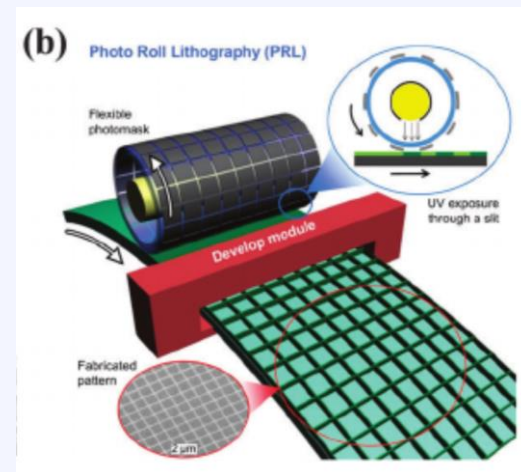
- Wider acceptance angle
- May not need to be moved as much

 relax tracking system.

Long term vision:



Nanoimprint

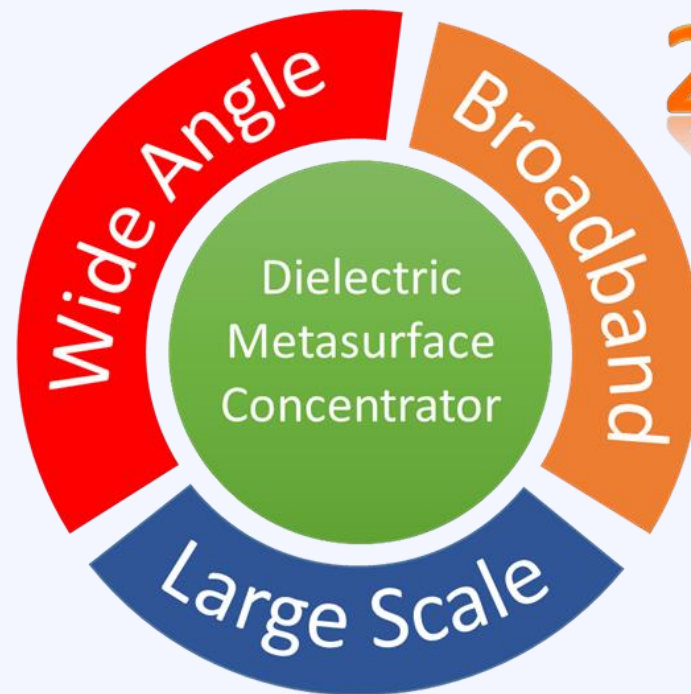


Roll-to-roll fabrication

# Challenges

1

- $\Phi \approx 2\pi$
- $\theta \geq 40^\circ$
- Optimization
- Experiments



2

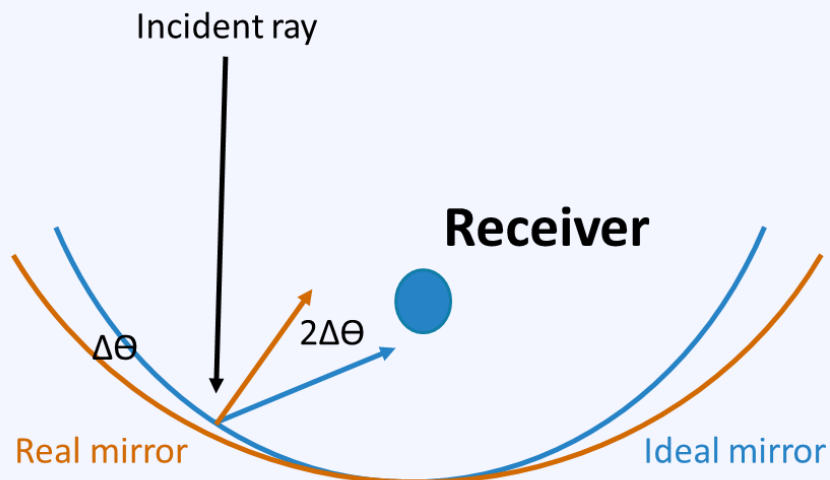
- Frequency-dependent
- $BW \geq 15\%$
- $BW \geq 15\%$  and  $\theta \geq 40^\circ$
- Experiments

3

- From mm to m
- Lifetime extension
- Integration
- Experiments

# From parabolic trough to metasurface concentrator

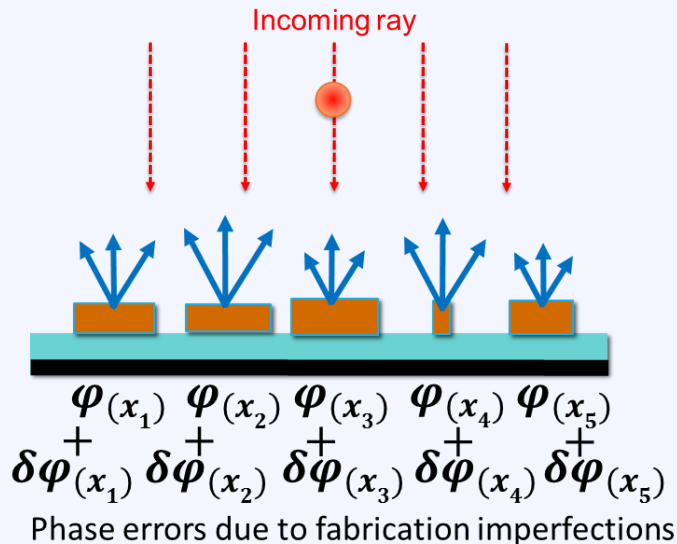
## Geometric optics concentrator



Slope error:  $\Delta\theta$



## Metasurface concentrator



$$\text{Slope error} : \frac{1}{k_0} \frac{d\delta\varphi}{dx}$$

(a unitless phase gradient error)

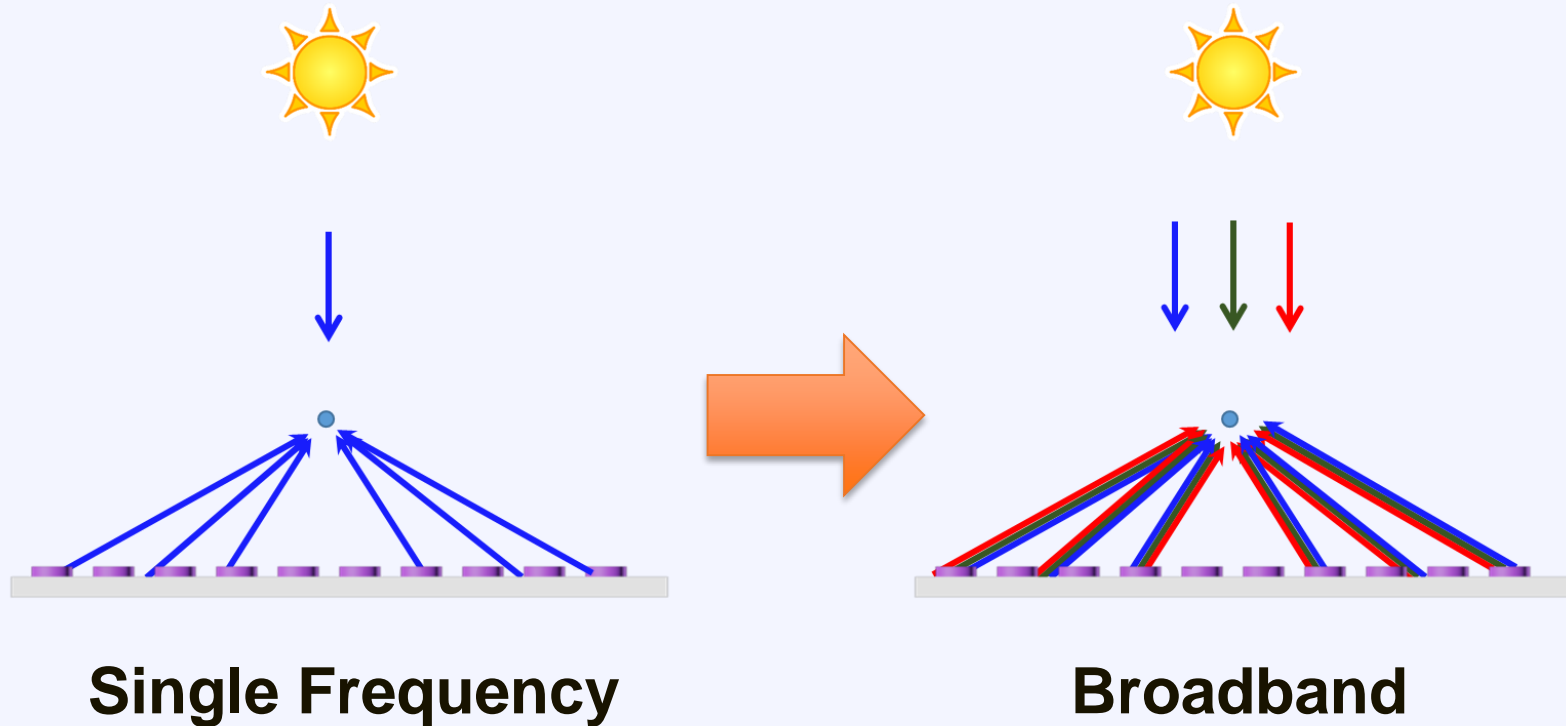
$$\text{Intercept factor } \gamma = \frac{\text{Energy incident on the receiver (with phase noise)}}{\text{Energy incident on the receiver (without phase noise)}}$$

$$\text{Intercept factor } \gamma = \frac{\text{\# of rays intercepts the receiver}}{\text{total \# of rays}}$$



$$\gamma > 0.9$$

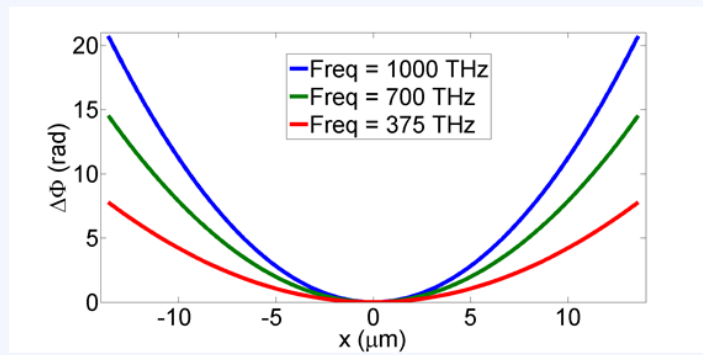
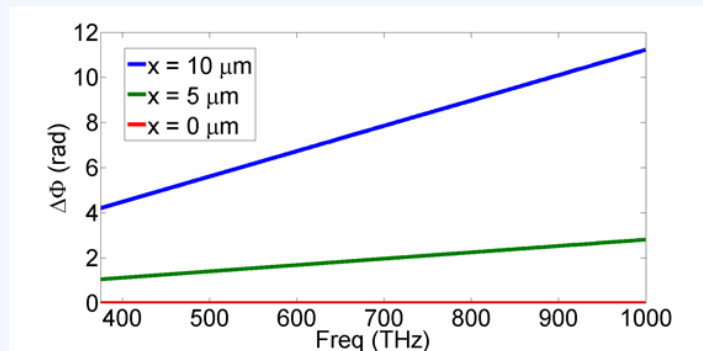
# Broadband Metasurfaces



Hsu, B. Kanté *et al.* Opt. Letters , 1520 (2017)

# Requirement and challenges for broadband metasurface concentrator

$$\Delta\Phi = \frac{2\pi\nu}{c} \left( \sqrt{x^2 + f^2} - f \right)$$



1. Linear phase shift with frequency ( $\nu$ ).

Solution:

- Propagating mode with constant effective refractive index.

2. Control slopes of the phase shift.

Solution:

- Propagating length or effective index.

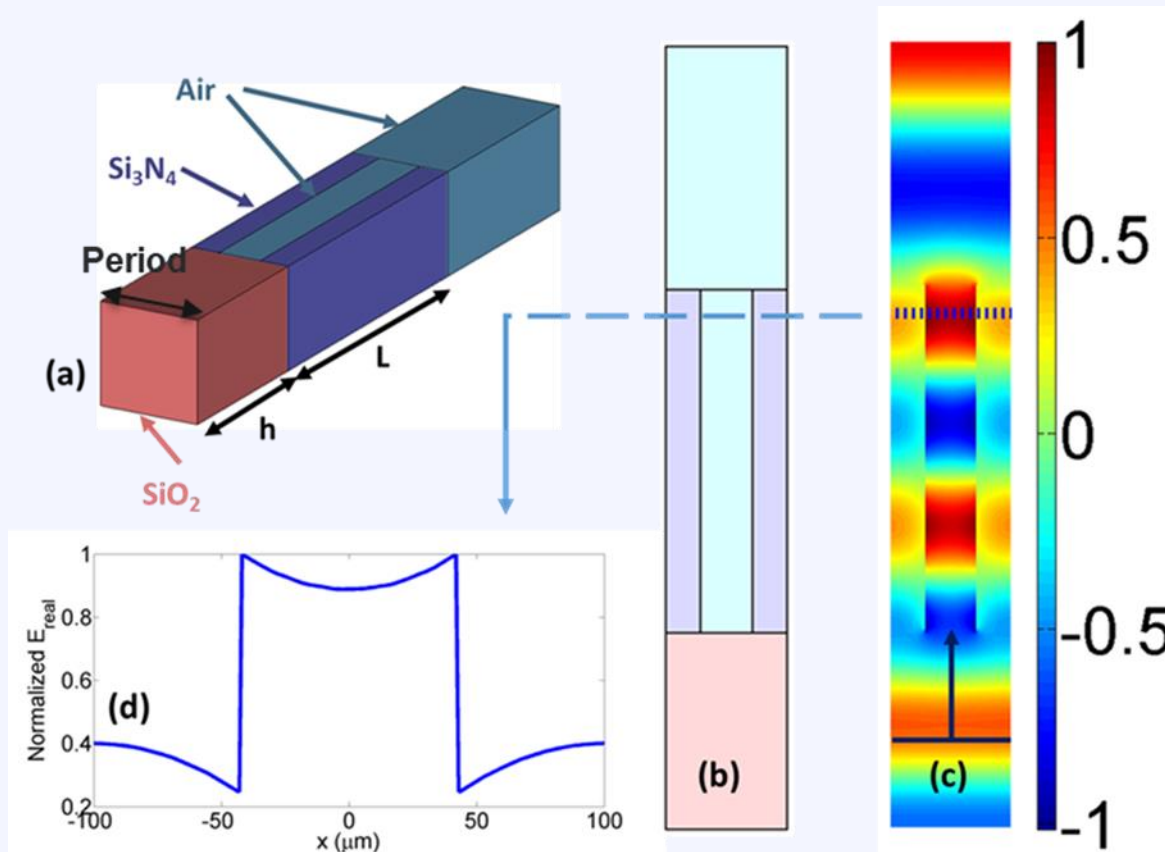
3. Zero phase shift intercept.  
(Constant phase-intercept).

Solution:

- Propagating length or effective index.

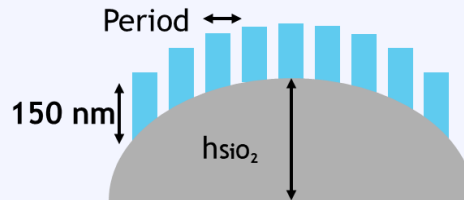


# Proposed design for metasurface: Slot waveguide



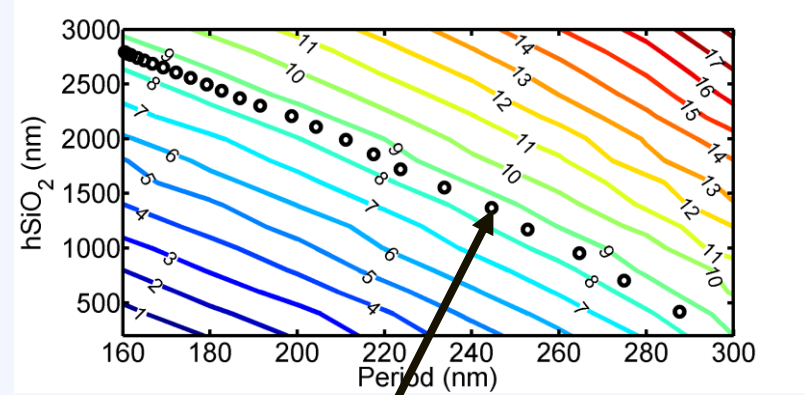
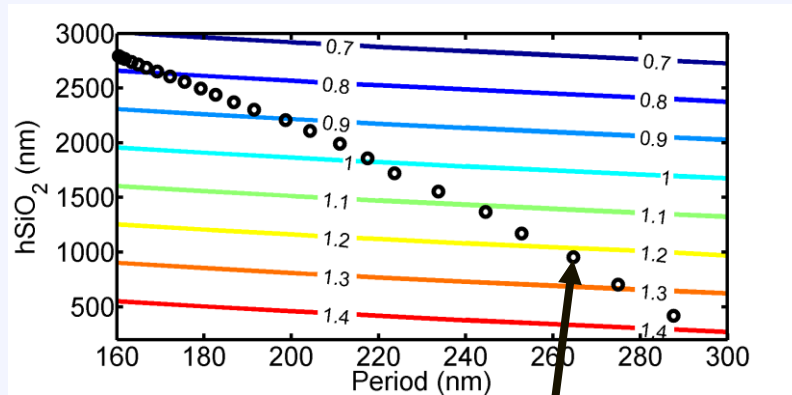
- **Mode confined in air**  
Less dispersion
- **Linear polarization**  
Higher efficiency.

# Slope and phase shift intercept



Slope

Phase Intercept

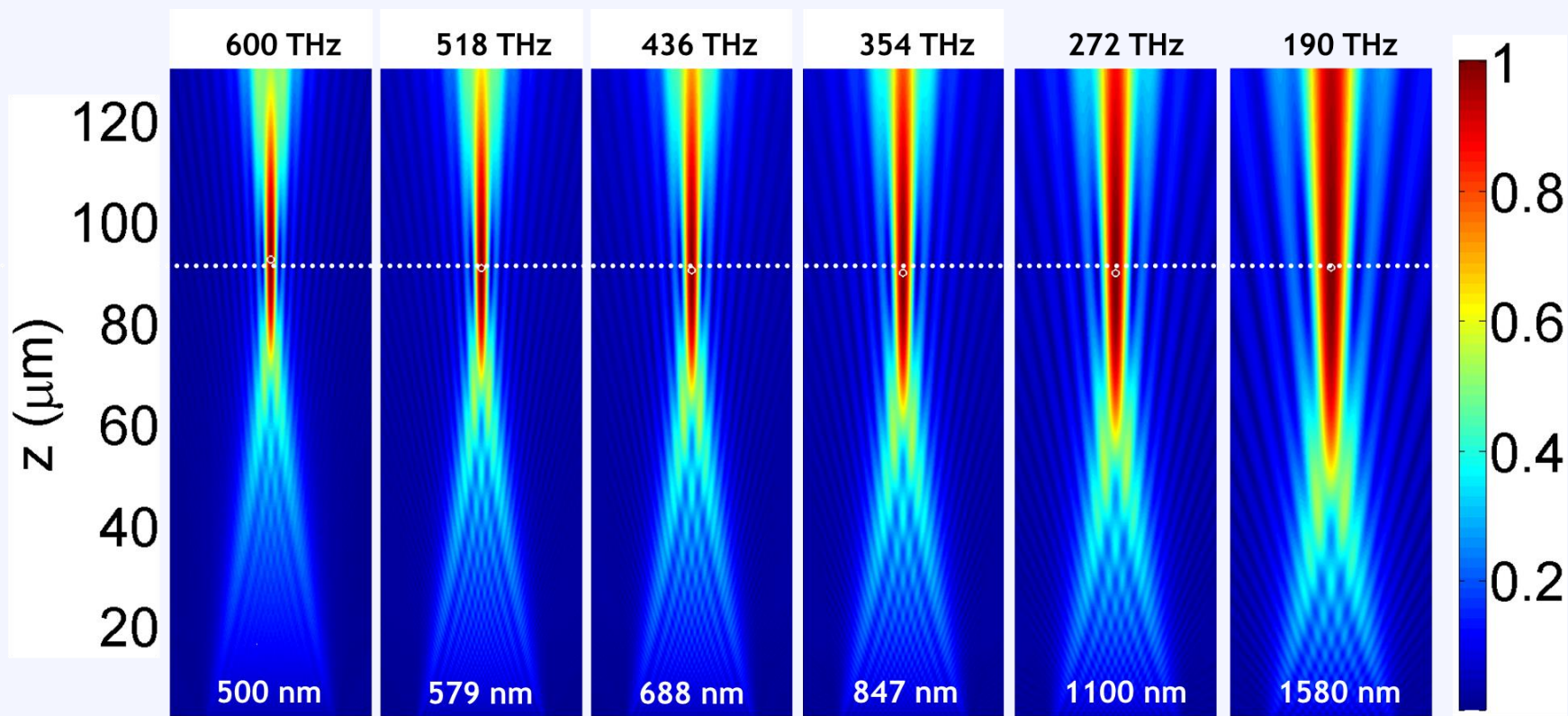


Different Slopes

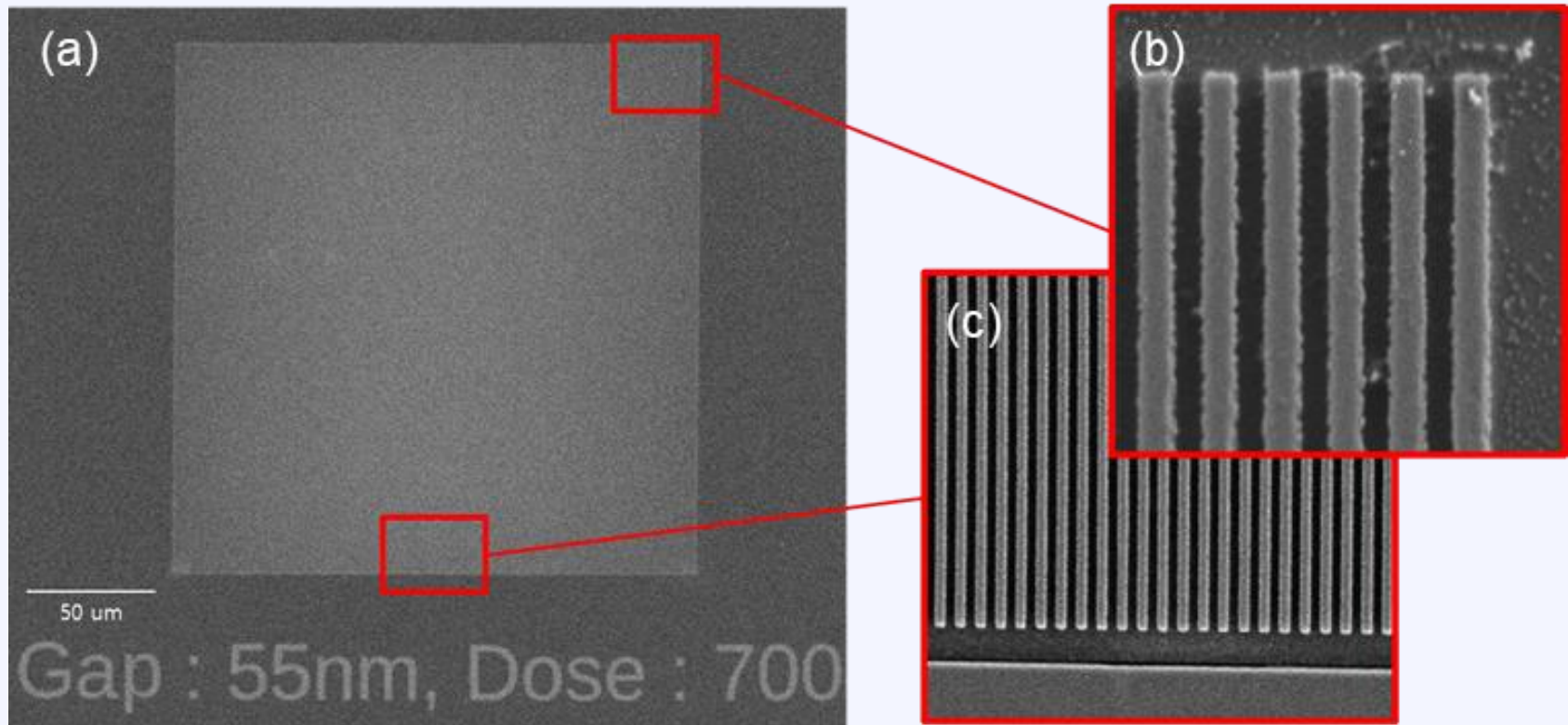
Constant Phase Intercept

**Bandwidth [ 500nm-1580 nm] (100%)**

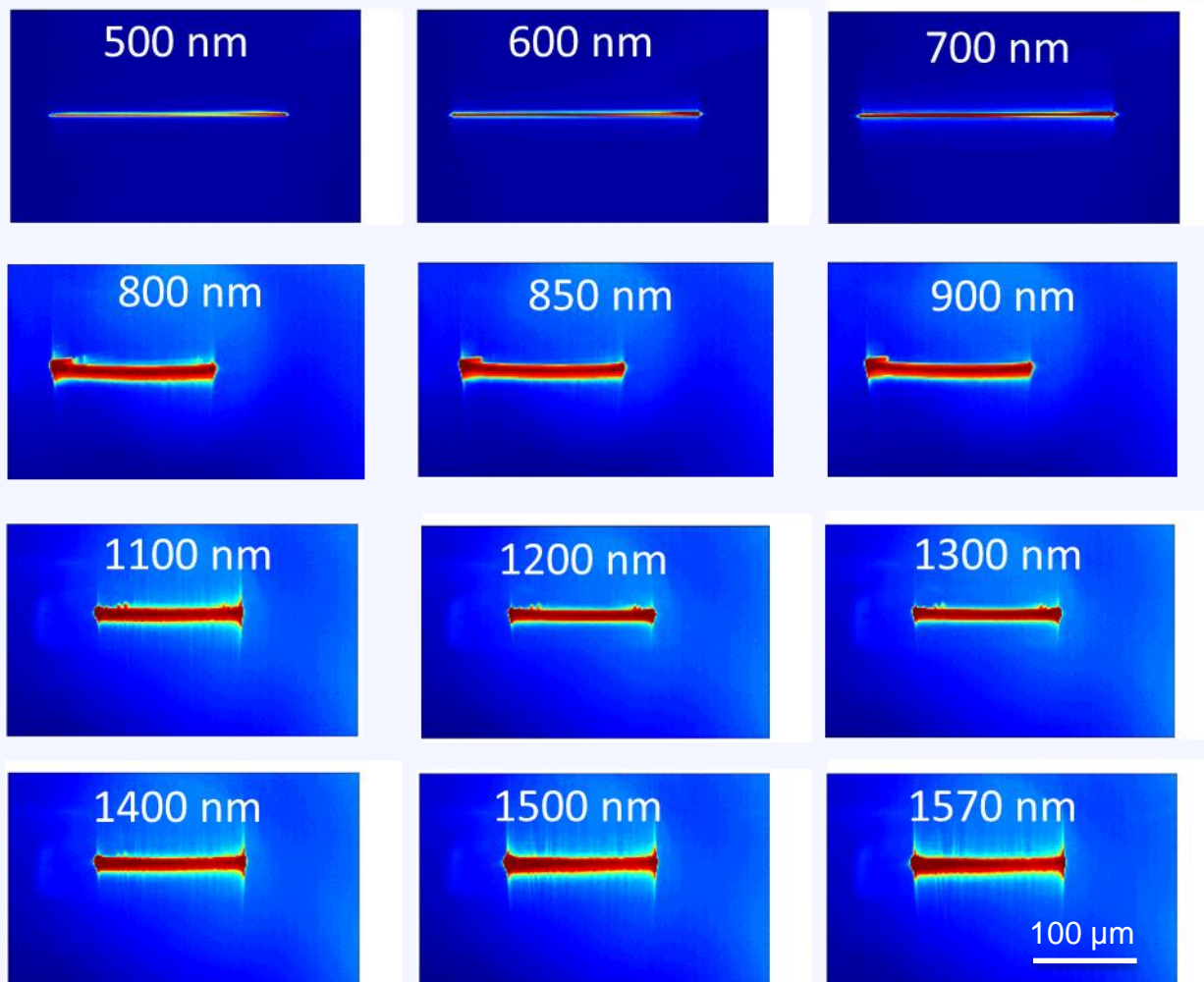
# Simulation Results (E-field)



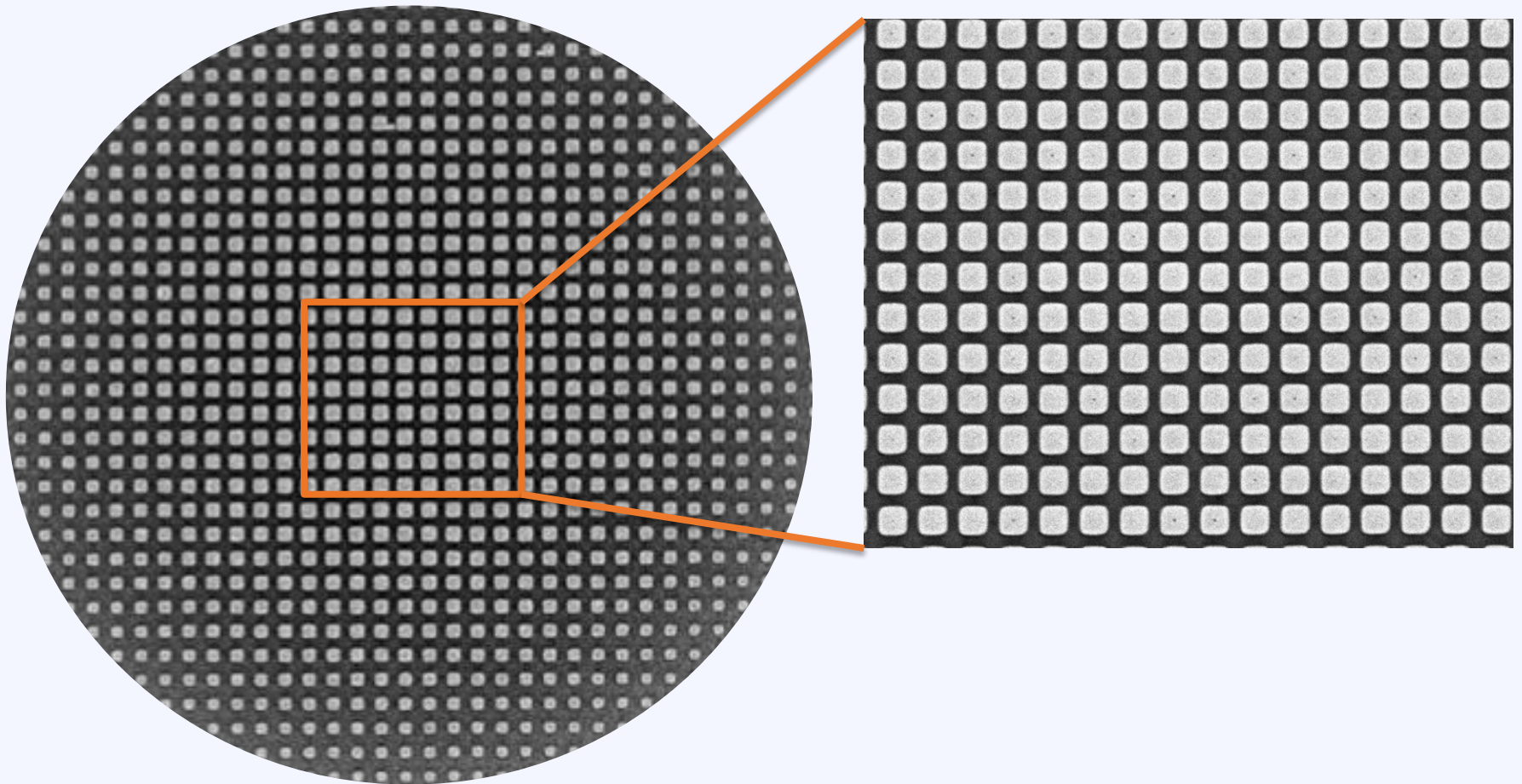
# Fabrication Results (SEM images)



# Measurement Results

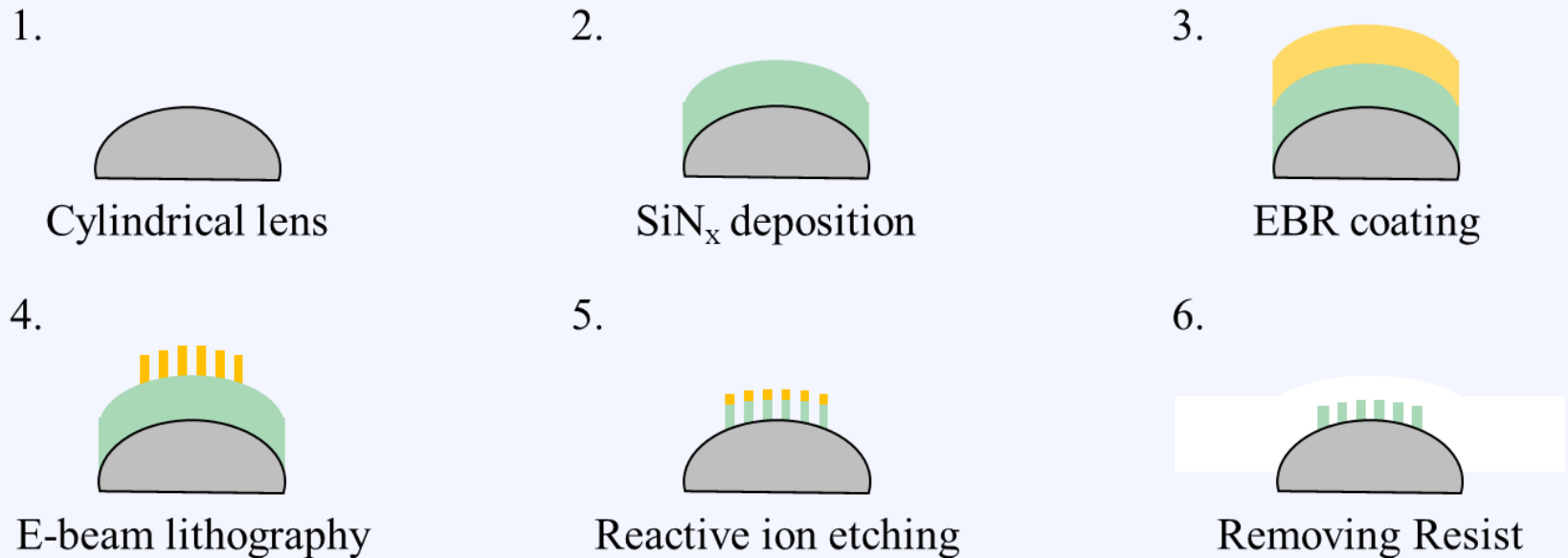


# SEM image for polarization insensitive



**Thank you.**

# Fabrication flow chart

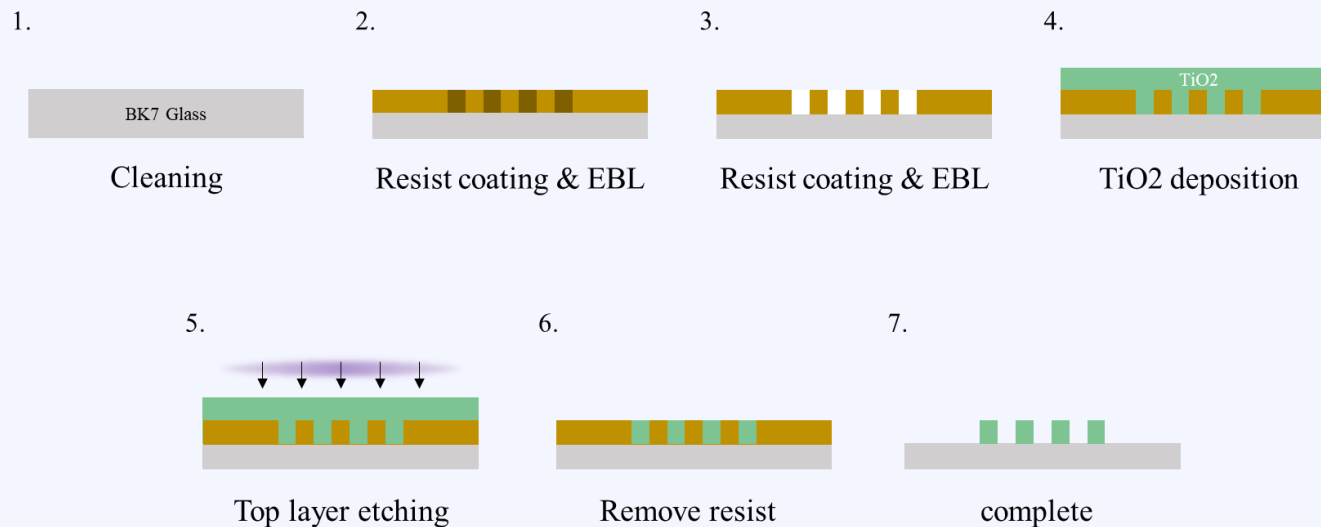


1. Cleaning (acetone, IPA, DI water)
2. SiN<sub>x</sub> deposition (150 nm) by the PECVD (350 C)
3. EBR coating for EBL(E-beam lithography) process (PMMA A2, 100 nm thickness)
4. EBL patterning (Vistec EBPG 5200)
5. RIE(Reactive ion etch) process for the SiN<sub>x</sub> etching
6. Remove residues of resist (by solvents or sulfuric acid and O<sub>2</sub> plasma)



# Fabrication flow chart

- lift-off, change the material SiNx to TiO<sub>2</sub> and thickness



1. Cleaning (Acetone, IPA, DI water)
2. EBR coating for EBL(E-beam lithography) process (PMMA C4 for 500 nm, A2 for 350 nm)
3. EBL patterning (Vistec EBPG 5200) to fabricate the resist etching mask
4. TiO<sub>2</sub> deposition (500, 350 nm) by the ALD (TiCl<sub>4</sub> + H<sub>2</sub>O precursor, 100 C)
5. RIE(Reactive ion etch) process to reveal the resist patterns
6. Remove residues of resist (by solvents and O<sub>2</sub> plasma)